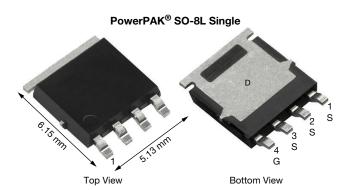


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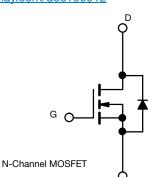
Automotive N-Channel 200 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY						
V _{DS} (V)	200					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.145					
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.150					
I _D (A)	13					
Configuration	Single					

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912







ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ454EP (for detailed order number please see www.vishay.com/doc?79771)

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	200	.,,	
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current	T _C = 25 °C	1	13		
Continuous drain current	T _C = 125 °C	I _D	7.5		
Continuous source current (diode	conduction) ^a	I _S	60	А	
Pulsed drain current b		I _{DM}	30		
Single pulse avalanche current L = 0.1 mH		I _{AS}	15		
Single pulse avalanche energy	L=0.11IIII	E _{AS}	11.2	mJ	
Maximum power dissipation ^b	T _C = 25 °C	Б	68	W	
Maximum power dissipation ~	T _C = 125 °C	P_{D}	22	VV	
Operating junction and storage temperature	T _J , T _{stg}	-55 to +175	°C		
Soldering recommendations (peak temperat	-	260	-0		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient F	PCB mount c	R_{thJA}	68	°C/W		
Junction-to-case (drain)		R _{thJC}	2.2	C/VV		

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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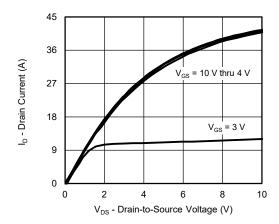
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static		•						
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_{D} = 250 \mu A$		200	-	-	.,,	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 200 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 200 V, T _J = 125 °C	1	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 200 V, T _J = 175 °C	-	-	250		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	10	-	-	Α	
		V _{GS} = 10 V	I _D = 7.5 A	-	0.118	0.145		
	_	V _{GS} = 4.5 V	I _D = 5 A	-	0.123	0.150		
Drain-source on-state resistance a	$R_{DS(on)}$	V _{GS} = 10 V	I _D = 7.5 A, T _J = 125 °C	-	-	0.298	Ω	
		V _{GS} = 10 V	I _D = 7.5 A, T _J = 175 °C	-	-	0.394		
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 7.5 A		-	33	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	1990	2600	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	133	180		
Reverse transfer capacitance	C _{rss}			-	62	85		
Total gate charge ^c	Qg			-	56	85	nC	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 100 \text{ V}, I_D = 2 \text{ A}$	-	7	-		
Gate-drain charge ^c	Q _{gd}			-	15	-		
Gate resistance	Rg		f = 1 MHz	0.20	0.45	0.80	Ω	
Turn-on delay time ^c	t _{d(on)}			-	14	25		
Rise time ^c	t _r	V _{DD} =	= 100 V, R _I = 50 Ω	1	5	10		
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 2 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	33	55	ns ns	
Fall time ^c	t _f			-	8	15		
	Source-Drain	Diode Ratings ar	nd Characteristics b				ı	
Pulsed current ^a	I _{SM}			-	-	30	Α	
Forward voltage	V_{SD}	I _F = 7.5 A, V _{GS} = 0		-	0.83	1.2	V	
Body diode reverse recovery time	t _{rr}	- I _F = 5 A, di/dt = 100 A/μs		-	86	175	ns	
Body diode reverse recovery charge	Q _{rr}			-	335	700	nC	
Reverse recovery fall time	t _a			-	64	-		
Reverse recovery rise time	t _b	1	-	22	-	ns		
Body diode peak reverse recovery current	I _{RM(REC)}		-	-7.6	-	Α		

Notes

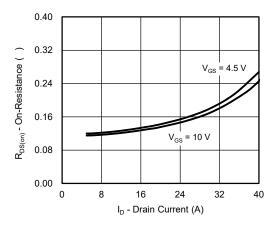
- f. Pulse test; pulse width $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- g. Guaranteed by design, not subject to production testing.
- h. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

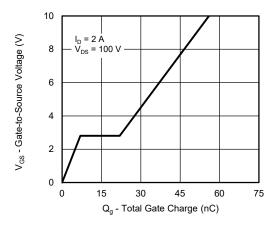




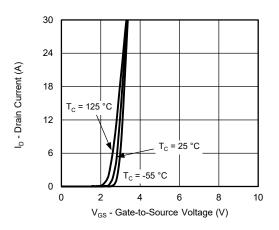
Output Characteristics



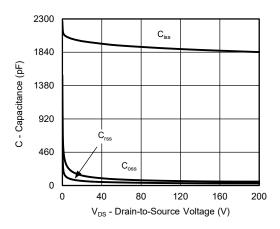
On-Resistance vs. Drain Current



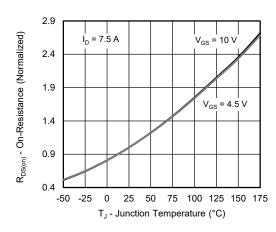
Gate Charge



Transfer Characteristics



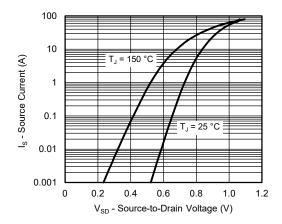
Capacitance



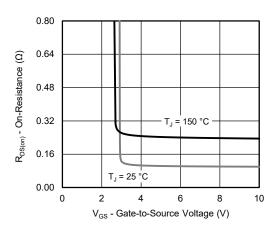
On-Resistance vs. Junction Temperature

For technical questions, contact: automoste

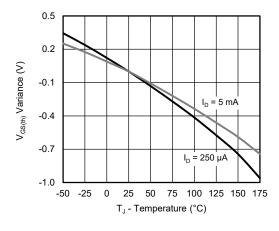




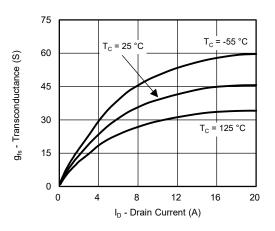
Source Drain Diode Forward Voltage



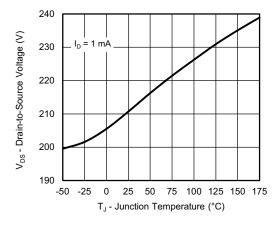
On-Resistance vs. Gate-to Source Voltage



Threshold Voltage



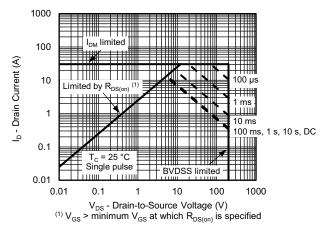
Transconductance



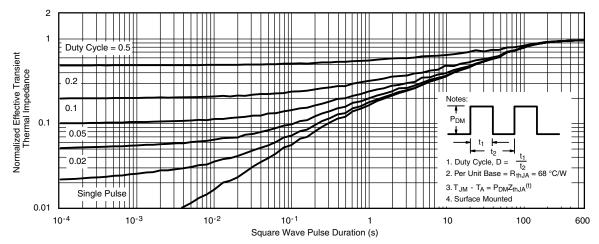
Drain Source Breakdown vs. Junction Temperature

For technical questions, contact: automostech



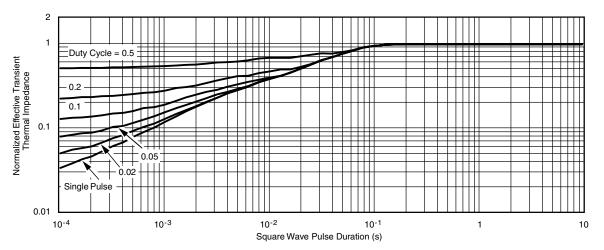


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient





Normalized Thermal Transient Impedance, Junction-to-Case

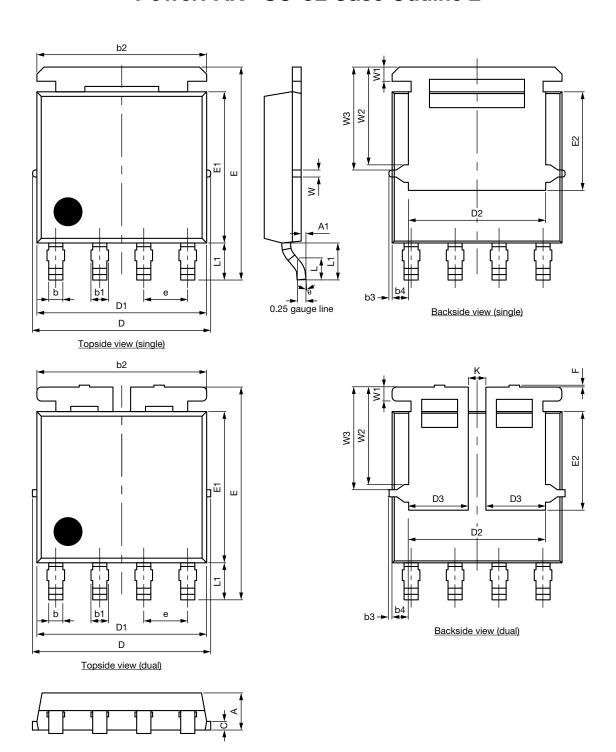
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75925.



PowerPAK® SO-8L Case Outline 2



Vishay Siliconix

DIM.		MILLIMETERS			INCHES		
DIN.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004	•	
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W	0.23				0.009		
W1	0.41			0.016			
W2	2.82			0.111			
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

ECN: C21-1498-Rev. C, 01-Nov-2021

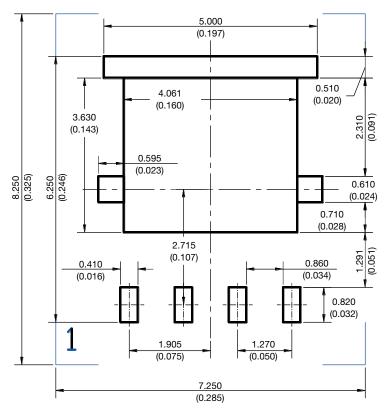
DWG: 6044

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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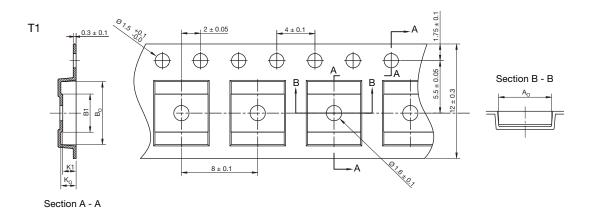
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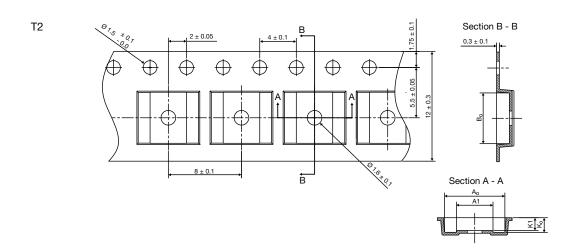
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PowerPAK® SO-8L Carrier Tape





Version	A _O	A1	B _O	B1	K _O	K1	Quantity per reel
T1 / - 1	5.55 ± 0.1	-	6.60 ± 0.1	4 ± 0.15	1.6 ± 0.1	1.4 ± 0.1	3000
T2 / - 2 ^a	6.60 ± 0.1	4 ± 0.15	5.55 ± 0.1	-	1.6 ± 0.1	1.4 ± 0.1	3000

- a. Not standard offering. Please contact local sales office for availability.
- $^{(1)}$ 10 sprocket hole pitch cumulative tolerance \pm 0.2 mm.
- (2) Camber not to exceed 1 mm in 100 mm, also not to exceed 1.5 cm in 1 m actually.
- (3) Material: black conductive or black static dissipative.
- $^{(4)}$ A_o and B_o measured on a plane 0.3 mm above the bottom of the pocket.
- (5) K_o measured from a plane on the inside bottom of the pocket to the top surface of carrier.
- (6) It should be measured from:
 - a. sprocket hole to pocket center.
 - b. sprocket hole to pocket hole.
- (7) All size in mm unless specified.
- (8) Tolerance will be \pm 0.1 mm unless specified.
- (9) Vishay part number must be labeled at all reels of carrier tape.
- $^{(10)}$ Surface resistivity: 10^4 to 10^{11} Ω .
- (11) Version suffix as above table shown.

ECN: C15-1433-Rev. F, 02-Nov-15

DWG: 93-5259-X

Revision: 02-Nov-15 Document Number: 69632

SQ Automotive MOSFET Ordering Information

Vishay Siliconix

SQ Series Automotive MOSFET Ordering Code for Parts with Alternate Manufacturing Locations

Standard ordering code for SQ series of automotive MOSFETs can be derived per the following table:

PACKAGE TYPE	DATASHEET PART NUMBER	ORDERING SUFFIX	ORDERING PART NUMBER
PowerPAK® 1212	Datasheet part number (example: SQS401EN)	-T1_GE3, -T1_BE3 ^a	Datasheet part number + "-T1_GE3" or "-T1_BE3" (example: SQS401EN-T1_GE3, SQS401EN-T1_BE3)
PowerPAK [®] SO-8L	Datasheet part number (example: SQJ488EP)	-T1_GE3, -T1_BE3 ^a	Datasheet part number + "-T1_GE3" or "-T1_BE3" (example: SQJ488EP-T1_GE3, SQS488EP-T1_BE3)
SOT-23	Datasheet part number (example: SQ2309ES)	-T1_GE3, -T1_BE3 ^a	Datasheet part number + "-T1_GE3" or "-T1_BE3" (example: SQ2309ES-T1_GE3, SQ2309ES-T1_BE3)
TSOP-6	Datasheet part number (example: SQ3427EV)	-T1_GE3, -T1_BE3 ^a	Datasheet part number + "-T1_GE3" or "-T1_BE3" (example: SQ3427EV-T1_GE3, SQ3427EV-T1_BE3)
SO-8	Datasheet part number (example: SQ4182EY)	-T1_GE3, -T1_BE3 ^a	Datasheet part number + "-T1_GE3" or "-T1_BE3" (example: SQ4182EY-T1_GE3, SQ4182EY-T1_GE3)

Notes

For bare die parts and for non-standard orientations in tape (such as T2, T4) please contact your local sales or marketing for ordering code information

a. "_BE3" denotes alternate manufacturing location